Infineon Technologies - XMC1100T016F0016AAXUMA1 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	11
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 6x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-16-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t016f0016aaxuma1

XMC1100

Microcontroller Series
for Industrial Applications

XMC1000 Family

ARM® Cortex™-M0
32-bit processor core

Data Sheet

V1.4 2014-05

Microcontrollers

XMC1100 Data Sheet

Revision History: V1.4 2014-05

Previous Version: V1.3	
Page	Subjects
Page 10	ADC channels of Table 2 is updated. Table 3 is added.
Page 10	Description for Chip Identification Number of Section 1.4 is updated.
Page 17	The pad type is corrected for P1.6 in Table 6.
Page 29	The t_{C12} , f_{C12}, t_{C10}, f_{C10}, t_{C8} and f_{C8} parameters are updated in Table 12.
Page 32	Figure 8 is added.
Page 33	The t_{SR} and t_{TSAL} parameters are updated in Table 13.
Page 36	Parameter name for t_{PSER} is updated. The $N_{WSFLASH}$ parameter and test condition for t_{RET} are added to Table 16.
Page 39	The min value for V_{DDPBO} parameter is added to Table 18. Footnote 1 is updated.
Page 41	The Δf_{LTT} parameter is added to Table 19.
Page 47	Figure 13 is added.

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About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1100 series devices.

The document describes the characteristics of a superset of the XMC1100 series devices. For simplicity, the various device types are referred to by the collective term XMC1100 throughout this document.

XMC1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

Table 1 Synopsis of XMC1100 Device Types (cont'd)

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-Q040F0032	PG-VQFN-40-13	32	16
XMC1100-Q040F0064	PG-VQFN-40-13	64	16

1.3 Device Type Features

The following table lists the available features per device type.

Table 2 Features of XMC1100 Device Types[1)]

Derivative	ADC channel
XMC1100-T016	6
XMC1100-T038	12
XMC1100-Q024	8
XMC1100-Q040	12

1) Features that are not included in this table are available in all the derivatives

Table 3 ADC Channels

Package	VADC0 G0	VADC0 G1
PG-TSSOP-16	CH0..CH5	–
PG-TSSOP-38	CH0..CH7	CH1, CH5 .. CH7
PG-VQFN-24	CH0..CH7	–
PG-VQFN-40	CH0..CH7	CH1, CH5 .. CH7

1.4 Chip Identification Number

The Chip Identification Number allows software to identify the marking. It is a 8 words value with the most significant 7 words stored in Flash configuration sector 0 (CS0) at address location : 1000 $0F00_H$ (MSB) - 1000 $0F1B_H$ (LSB). The least significant word and most significant word of the Chip Identification Number are the value of registers DBGROMID and IDCHIP, respectively.

Table 4 XMC1100 **Chip Identification Number**

Derivative	Value	Marking
XMC1100-T016F0008	00011032 01CF00FF 00001F37 00000000 00000B00 00001000 00003000 $101ED083_H$	AA
XMC1100-T016F0016	00011032 01CF00FF 00001F37 00000000 00000B00 00001000 00005000 $101ED083_H$	AA
XMC1100-T016F0032	00011032 01CF00FF 00001F37 00000000 00000B00 00001000 00009000 $101ED083_H$	AA
XMC1100-T016F0064	00011032 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA
XMC1100-T016X0064	00011033 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA
XMC1100-T038F0016	00011012 01CF00FF 00001F37 00000000 00000B00 00001000 00005000 $101ED083_H$	AA
XMC1100-T038F0032	00011012 01CF00FF 00001F37 00000000 00000B00 00001000 00009000 $101ED083_H$	AA
XMC1100-T038F0064	00011012 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA
XMC1100-T038X0064	00011013 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA
XMC1100-Q024F0008	00011062 01CF00FF 00001F37 00000000 00000B00 00001000 00003000 $101ED083_H$	AA
XMC1100-Q024F0016	00011062 01CF00FF 00001F37 00000000 00000B00 00001000 00005000 $101ED083_H$	AA
XMC1100-Q024F0032	00011062 01CF00FF 00001F37 00000000 00000B00 00001000 00009000 $101ED083_H$	AA
XMC1100-Q024F0064	00011062 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA
XMC1100-Q040F0016	00011042 01CF00FF 00001F37 00000000 00000B00 00001000 00005000 $101ED083_H$	AA
XMC1100-Q040F0032	00011042 01CF00FF 00001F37 00000000 00000B00 00001000 00009000 $101ED083_H$	AA
XMC1100-Q040F0064	00011042 01CF00FF 00001F37 00000000 00000B00 00001000 00011000 $101ED083_H$	AA

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

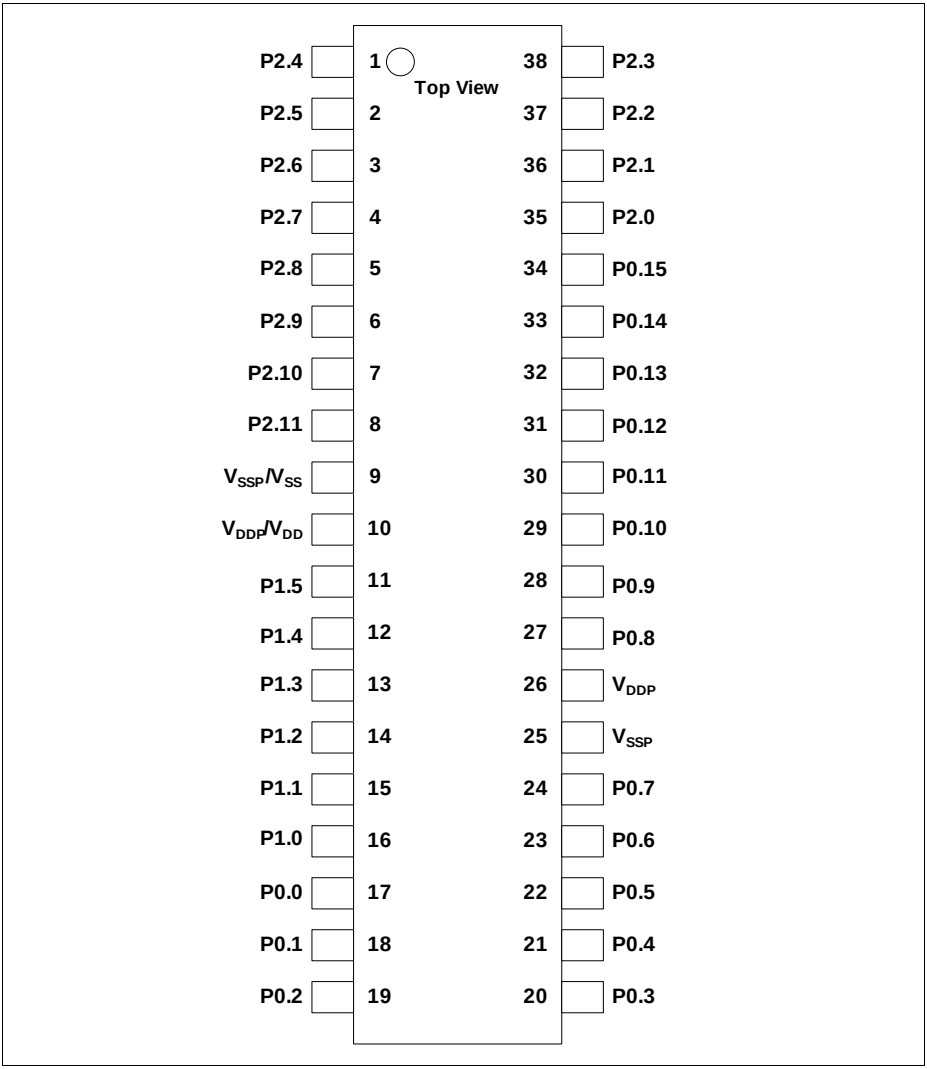

Figure 4 XMC1100 **PG-TSSOP-38 Pin Configuration** (top view)

2.2.1 Package Pin Summary

The following general building block is used to describe each pin:

Table 5 Package Pin Mapping Description

Function	Package A	Package B	...	Pad Type
Px.y	N	N		Pad Class

The table is sorted by the “Function” column, starting with the regular Port pins (Px.y), followed by the supply pins.

The following columns, titled with the supported package variants, lists the package pin number to which the respective function is mapped in that package.

The “Pad Type” indicates the employed pad type:

- STD_INOUT (standard bi-directional pads)
- STD_INOUT/AN (standard bi-directional pads with analog input)
- High Current (high current bi-directional pads)
- STD_IN/AN (standard input pads with analog input)
- Power (power supply)

Details about the pad properties are defined in the Electrical Parameters.

Table 6 Package Pin Mapping

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.0	23	17	15	7	STD_INOUT	
P0.1	24	18	-	-	STD_INOUT	
P0.2	25	19	-	-	STD_INOUT	
P0.3	26	20	-	-	STD_INOUT	
P0.4	27	21	-	-	STD_INOUT	
P0.5	28	22	16	8	STD_INOUT	
P0.6	29	23	17	9	STD_INOUT	
P0.7	30	24	18	10	STD_INOUT	
P0.8	33	27	19	11	STD_INOUT	
P0.9	34	28	20	12	STD_INOUT	
P0.10	35	29	-	-	STD_INOUT	
P0.11	36	30	-	-	STD_INOUT	
P0.12	37	31	21	-	STD_INOUT	

Table 6 Package Pin Mapping

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	-	STD_INOUT	
P0.14	39	33	23	13	STD_INOUT	
P0.15	40	34	24	14	STD_INOUT	
P1.0	22	16	14	-	High Current	
P1.1	21	15	13	-	High Current	
P1.2	20	14	12	-	High Current	
P1.3	19	13	11	-	High Current	
P1.4	18	12	-	-	High Current	
P1.5	17	11	-	-	High Current	
P1.6	16	-	-	-	STD_INOUT	
P2.0	1	35	1	15	STD_INOUT/AN	
P2.1	2	36	2	-	STD_INOUT/AN	
P2.2	3	37	3	-	STD_IN/AN	
P2.3	4	38	-	-	STD_IN/AN	
P2.4	5	1	-	-	STD_IN/AN	
P2.5	6	2	-	-	STD_IN/AN	
P2.6	7	3	4	16	STD_IN/AN	
P2.7	8	4	5	1	STD_IN/AN	
P2.8	9	5	5	1	STD_IN/AN	
P2.9	10	6	6	2	STD_IN/AN	
P2.10	11	7	7	3	STD_INOUT/AN	
P2.11	12	8	8	4	STD_INOUT/AN	
VSS	13	9	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage. VDD has to be supplied with the same voltage as VDDP

2.2.2 Port I/O Functions

The following general building block is used to describe each PORT pin:

Table 7 Port I/O Function Description

Function	Outputs			Inputs		
	ALT1	ALTn	HWO0	HWI0	Input	Input
P0.0		MODA.OUT	MODB.OUT	MODB.INA	MODC.INA	
Pn.y	MODA.OUT				MODA.INA	MODC.INB

Pn.y is the port pin name, defining the control and data bits/registers associated with it. As GPIO, the port is under software control. Its input value is read via Pn_IN.y, Pn_OUT defines the output value.

Up to seven alternate output functions (ALT1/2/3/4/5/6/7) can be mapped to a single port pin, selected by Pn_IOCR.PC. The output value is directly driven by the respective module, with the pin characteristics controlled by the port registers (within the limits of the connected pad).

The port pin input can be connected to multiple peripherals. Most peripherals have an input multiplexer to select between different possible input sources.

The input path is also active while the pin is configured as output. This allows to feedback an output to on-chip resources without wasting an additional external pin.

By Pn_HWSEL, it is possible to select between different hardware “masters” (HWO0/HWI0, HWO1/HWI1). The selected peripheral can take control of the pin(s). Hardware control overrules settings in the respective port pin registers.

3.2 DC Parameters

3.2.1 Input/Output Characteristics

Table 11 provides the characteristics of the input/output pins of the XMC1100.

Table 11 Input/Output Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Output low voltage on port pins (with standard pads)	V_{OLP}	CC	–	1.0	V	I_{OL} = 11 mA (5 V) I_{OL} = 7 mA (3.3 V)
			–	0.4	V	I_{OL} = 5 mA (5 V) I_{OL} = 3.5 mA (3.3 V)
Output low voltage on high current pads	V_{OLP1}	CC	–	1.0	V	I_{OL} = 50 mA (5 V) I_{OL} = 25 mA (3.3 V)
			–	0.32	V	I_{OL} = 10 mA (5 V)
			–	0.4	V	I_{OL} = 5 mA (3.3 V)
Output high voltage on port pins (with standard pads)	V_{OHP}	CC	V_{DDP} - 1.0	–	V	I_{OH} = -10 mA (5 V) I_{OH} = -7 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4.5 mA (5 V) I_{OH} = -2.5 mA (3.3 V)
Output high voltage on high current pads	V_{OHP1}	CC	V_{DDP} - 0.32	–	V	I_{OH} = -6 mA (5 V)
			V_{DDP} - 1.0	–	V	I_{OH} = -8 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4 mA (3.3 V)
Input low voltage on port pins (Standard Hysteresis)	V_{ILPS}	SR	–	0.19 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)
Input high voltage on port pins (Standard Hysteresis)	V_{IHPS}	SR	0.7 × V_{DDP}	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	0.08 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[3)]

Table 11 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Maximum current into V_{DDP} (TSSOP28/16, VQFN24)	I_{MVDD1}	SR	–	130	mA	3)
Maximum current into V_{DDP} (TSSOP38, VQFN40)	I_{MVDD2}	SR	–	260	mA	3)
Maximum current out of V_{SS} (TSSOP28/16, VQFN24)	I_{MVSS1}	SR	–	130	mA	3)
Maximum current out of V_{SS} (TSSOP38, VQFN40)	I_{MVSS2}	SR	–	260	mA	3)

1) Not subject to production test, verified by design/characterization. Hysteresis is implemented to avoid meta stable states and switching due to internal ground bounce. It cannot be guaranteed that it suppresses switching due to external system noise.

2) An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin.

3) Not subject to production test, verified by design/characterization.

4) Not subject to production test, verified by design/characterization. However, for applications with strict low power-down current requirements, it is mandatory that no active voltage source is supplied at any GPIO pin when V_{DDP} is powered off.

3.2.3 Temperature Sensor Characteristics

Table 13 Temperature Sensor Characteristics[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Measurement time	t_M CC	–	–	10	ms	
Temperature sensor range	T_{SR} SR	-40	–	115	°C	
Sensor Accuracy[2)]	T_{TSAL} CC	–	+/-20	–	°C	T_J = -40 °C (calibrated)
		–	+/-12	–	°C	T_J = -25 °C (calibrated)
		-5	–	5	°C	T_J = 0 °C
		-2	–	2	°C	T_J = 25 °C (calibrated)
		-4	–	4	°C	T_J = 70 °C
		-2	–	2	°C	T_J = 115 °C (calibrated)

1) Not subject to production test, verified by design/characterization.

2) The temperature sensor accuracy is independent of the supply voltage.

Table 15 provides the active current consumption of some modules operating at 5 V power supply at 25 °C. The typical values shown are used as a reference guide on the current consumption when these modules are enabled.

Table 15 Typical Active Current Consumption[1)]

Active Current Consumption	Symbol	Limit Values	Unit	Test Condition
		Typ.		
Baseload current	I_{CPUDDC}	5.04	mA	Modules including Core, SCU, PORT, memories, ANATOP[2)]
VADC and SHS	I_{ADCDDC}	3.4	mA	Set CGATCLR0.VADC to 1[3)]
USIC0	$I_{USIC0DDC}$	0.87	mA	Set CGATCLR0.USIC0 to 1[4)]
CCU40	$I_{CCU40DDC}$	0.94	mA	Set CGATCLR0.CCU40 to 1[5)]
WDT	I_{WDTDDC}	0.03	mA	Set CGATCLR0.WDT to 1[6)]
RTC	I_{RTCDDC}	0.01	mA	Set CGATCLR0.RTC to 1[7)]

1) Not subject to production test, verified by design/characterisation.

2) Baseload current is measured with device running in user mode, MCLK=PCLK=32 MHz, with an endless loop in the flash memory. The clock to the modules stated in CGATSTAT0 are gated.

3) Active current is measured with: module enabled, MCLK=32 MHz, running in auto-scan conversion mode

4) Active current is measured with: module enabled, alternating messages sent to PC at 57.6kbaud every 200ms

5) Active current is measured with: module enabled, MCLK=PCLK=32 MHz, 1 CCU4 slice for PWM switching from 1500Hz and 1000Hz at regular intervals, 1 CCU4 slice in capture mode for reading period and duty cycle

6) Active current is measured with: module enabled, MCLK=32 MHz, time-out mode; WLB = 0, WUB = 0x00008000; WDT serviced every 1s

7) Active current is measured with: module enabled, MCLK=32 MHz, Periodic interrupt enabled

3.2.5 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 16 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Erase Time per page	t_{ERASE} CC	6.8	7.1	7.6	ms	
Program time per block	t_{PSER} CC	102	152	204	µs	
Wake-Up time	t_{WU} CC	–	32.2	–	µs	
Read time per word	t_a CC	–	50	–	ns	
Data Retention Time	t_{RET} CC	10	–	–	years	Max. 100 erase / program cycles
Flash Wait States [1]	$N_{WSFLASH}$ CC	0	0.5	–		f_{MCLK} = 8 MHz
		0	1.4	–		f_{MCLK} = 16 MHz
		1	1.9	–		f_{MCLK} = 32 MHz
Erase Cycles per page	N_{ECYC} CC	–	–	$5*10^4$	cycles	
Total Erase Cycles	N_{TECYC} CC	–	–	$2*10^6$	cycles	

1) Flash wait states are automatically inserted by the Flash module during memory read when needed. Typical values are calculated from the execution of the Dhrystone benchmark program.

3.3.3 Power-Up and Supply Threshold Charcteristics

Table 18 provides the characteristics of the supply threshold in XMC1100.

Table 18 Power-Up and Supply Threshold Parameters (Operating Conditions apply) [1]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
V_{DDP} ramp-up time	t_{RAMPUP} SR	V_{DDP}/ $S_{VDDPrise}$	–	10^7	µs	
V_{DDP} slew rate	S_{VDDPOP} SR	0	–	0.1	V/µs	Slope during normal operation
	S_{VDDP10} SR	0	–	10	V/µs	Slope during fast transient within +/- 10% of V_{DDP}
	$S_{VDDPrise}$ SR	0	–	10	V/µs	Slope during power-on or restart after brownout event
	$S_{VDDPfall}$ [2] SR	0	–	0.25	V/µs	Slope during supply falling out of the +/-10% limits[3]
V_{DDP} prewarning voltage	V_{DDPPW} CC	2.1	2.25	2.4	V	ANAVDEL.VDEL_ SELECT = 00_B
		2.85	3	3.15	V	ANAVDEL.VDEL_ SELECT = 01_B
		4.2	4.4	4.6	V	ANAVDEL.VDEL_ SELECT = 10_B
V_{DDP} brownout reset voltage	V_{DDPBO} CC	1.55	1.62	1.75	V	calibrated, before user code starts running
Start-up time from power-on reset	t_{SSW} SR	–	320	–	µs	Time to the first user code instruction[4]

1) Not all parameters are 100% tested, but are verified by design/characterisation.

2) A capacitor of at least 100 nF has to be added between V_{DDP} and V_{SSP} to fulfill the requirement as stated for this parameter.

3.3.4 On-Chip Oscillator Characteristics

Table 19 provides the characteristics of the 64 MHz clock output from the digital controlled oscillator, DCO1 in XMC1100.

Table 19 64 MHz DCO1 Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values			Unit	Test Conditions
			Min.	Typ.	Max.		
Nominal frequency	f_{NOM}	CC	63.5	64	64.5	MHz	under nominal conditions[1] after trimming
Accuracy	Δf_{LT}	CC	-1.7	–	3.4	%	with respect to f_{NOM}(typ), over temperature (0 °C to 85 °C)[2]
			-3.9	–	4.0	%	with respect to f_{NOM}(typ), over temperature (-40 °C to 105 °C)[2]
Accuracy with calibration based on temperature sensor	Δf_{LTT}	CC	-1.3	–	1.25	%	with respect to f_{NOM}(typ), over temperature (T_A = 0 °C to 105 °C)[2]
			-2.6	–	1.25	%	with respect to f_{NOM}(typ), over temperature (T_A = -40 °C to 105 °C)[2]

1) The deviation is relative to the factory trimmed frequency at nominal V_{DDC} and T_A = + 25 °C.

2) Not subject to production test, verified by design/characterisation.

3.3.5 Serial Wire Debug Port (SW-DP) Timing

The following parameters are applicable for communication through the SW-DP interface.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 21 SWD Interface Timing Parameters(Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
SWDCLK high time	t_1 SR	50	–	500000	ns	–
SWDCLK low time	t_2 SR	50	–	500000	ns	–
SWDIO input setup to SWDCLK rising edge	t_3 SR	10	–	–	ns	–
SWDIO input hold after SWDCLK rising edge	t_4 SR	10	–	–	ns	–
SWDIO output valid time after SWDCLK rising edge	t_5 CC	–	–	68	ns	C_L = 50 pF
		–	–	62	ns	C_L = 30 pF
SWDIO output hold time from SWDCLK rising edge	t_6 CC	4	–	–	ns	

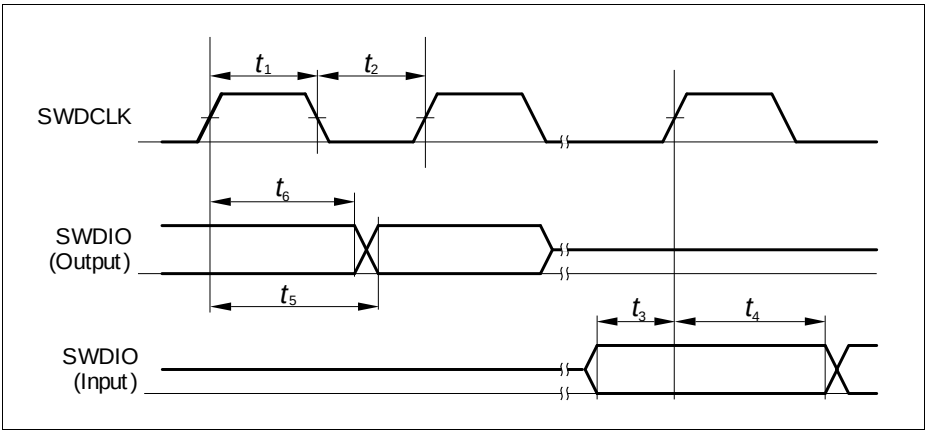

Figure 14 SWD Timing

3.3.6 SPD Timing Requirements

The optimum SPD decision time between 0_B and 1_B is 0.75 µs. With this value the system has maximum robustness against frequency deviations of the sampling clock on tool and on device side. However it is not always possible to exactly match this value with the given constraints for the sample clock. For instance for a oversampling rate of 4, the sample clock will be 8 MHz and in this case the closest possible effective decision time is 5.5 clock cycles (0.69 µs).

Table 22 Optimum Number of Sample Clocks for SPD

Sample Freq.	Sampling Factor	Sample Clocks 0_B	Sample Clocks 1_B	Effective Decision Time[1)]	Remark
8 MHz	4	1 to 5	6 to 12	0.69 µs	The other closest option (0.81 µs) for the effective decision time is less robust.

1) Nominal sample frequency period multiplied with 0.5 + (max. number of 0_B sample clocks)

For a balanced distribution of the timing robustness of SPD between tool and device, the timing requirements for the tool are:

- Frequency deviation of the sample clock is +/- 5%
- Effective decision time is between 0.69 µs and 0.75 µs (calculated with nominal sample frequency)

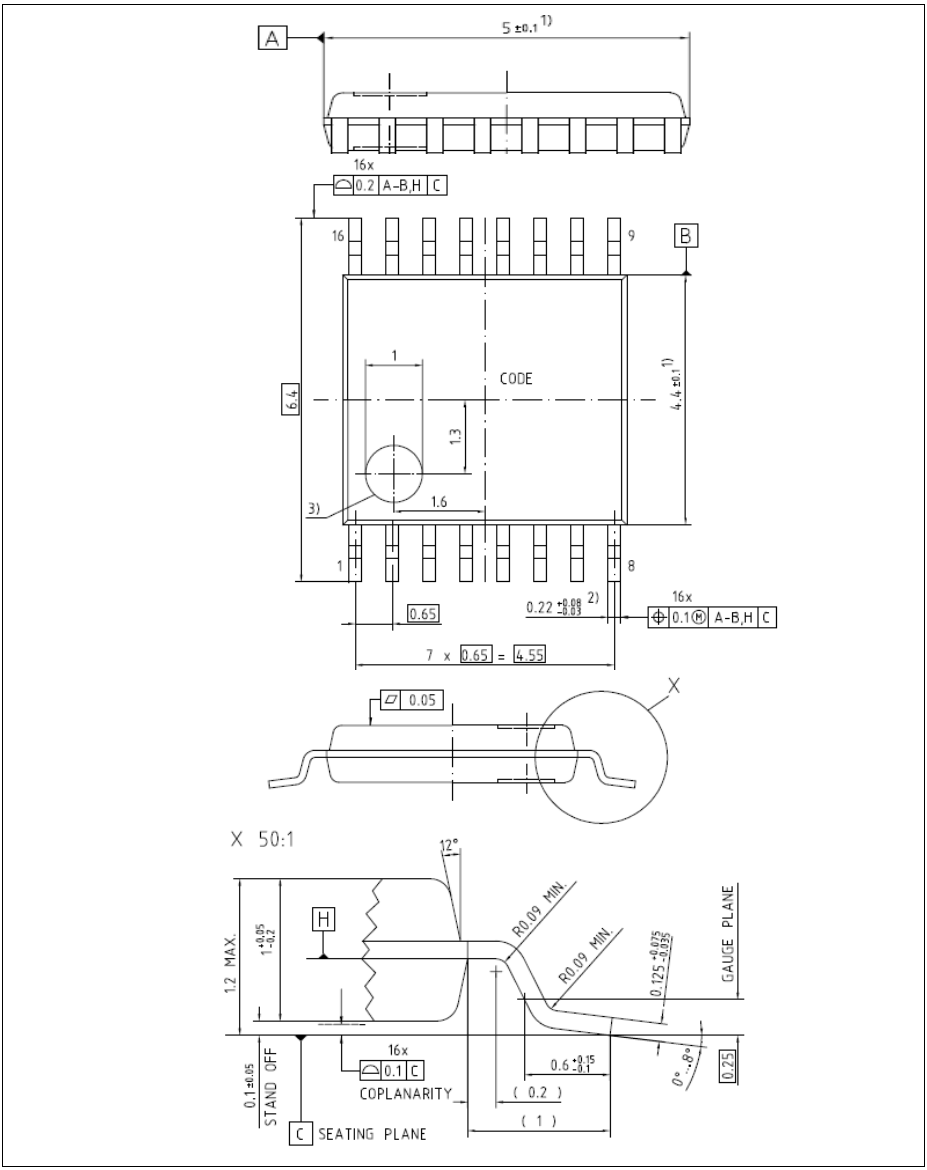

Figure 20 PG-TSSOP-16-8